

IN THE CLAIMS

Please substitute claims 1-19 with the following:

1. (Previously Presented) A semiconductor device comprising:
 - a first buried wiring;
 - a second buried wiring formed as a layer different from said first buried wiring;
 - a contact hole formed between said first buried wiring and said second buried wiring and
~~is~~ filled with a wiring material electrically connecting said first buried wiring and said second
buried wiring therethrough; and
 - a dummy hole formed to have a hole diameter substantially different from that of said
contact hole and in the vicinity of said contact hole so that a surface of said first buried wiring is
exposed to said dummy hole, wherein said dummy hole is adapted to cause a void to form in
association with said dummy hole when said dummy hole is at least partially filled with said
wiring material.
- 2.-3. (Canceled)
4. (Previously Presented) The semiconductor device according to claim 1, wherein said
second buried wiring is formed under said first buried wiring, and said dummy hole is formed
below said first buried wiring and said diameter of said dummy hole is substantially smaller than
said contact hole.

5. (Previously Presented) The semiconductor device according to claim 1, wherein said second buried wiring is formed over said first buried wiring, and said dummy hole is formed over said first buried wiring and said diameter of said dummy hole is substantially smaller than said contact hole.

6. (Original) The semiconductor device according to claim 1, wherein said wiring material is made of copper.

7. (Canceled)

8. (Previously Presented) The semiconductor device according to claim 4, wherein said diameter of said dummy hole is so set as to cause a plugging failure to form said void when said dummy hole is at least partially filled with said wiring material.

9. (Previously Presented) The semiconductor device according to claim 5, wherein said diameter of said dummy hole is so set as to cause a plugging failure to form said void when said dummy hole is at least partially filled with said wiring material.

10.-19. (Canceled)